

## 100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

75 A

#### **Features**

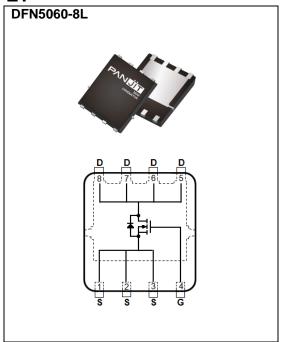
- RDS(ON), VGS@10V, ID@20A<7.4 $m\Omega$
- RDS(ON), VGS@4.5V, ID@10A<11m $\Omega$
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.08 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	100	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	v	
Continuous Drain Current(Note 3)	T <sub>C</sub> =25°C		75		
	T <sub>C</sub> =100°C	I <sub>D</sub>	53	Α	
Pulsed Drain Current(Note 1)	Tc=25°C	I <sub>DM</sub>	300		
Power Dissipation	Tc=25°C	D	83	W	
	T <sub>C</sub> =100°C	Po	42		
Continuous Drain Current(Note 4)	T <sub>A</sub> =25°C		15	А	
	T <sub>A</sub> =70°C	I <sub>D</sub>	12.6		
Power Dissipation	T <sub>A</sub> =25°C	PD	3.3	W	
	T <sub>A</sub> =70°C	PD	2.3		
Single Pulse Avalanche Current(Note 5)		I <sub>AS</sub>	40	Α	
Single Pulse Avalanche Energy <sup>(Note 5)</sup>		Eas	85	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C	
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	R <sub>0JC</sub>	1.8	°C/W	
	Junction to Ambient	RθJA	45		



### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

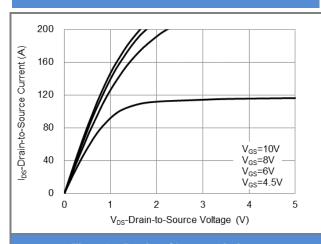
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	-	-	\/	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.5	2.1 3 V		V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	5.9	7.4	mΩ	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	8.4	11		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
Dynamic <sup>(Note 6)</sup>			•	•	•		
Total Gate Charge	$Q_g$	V <sub>DS</sub> =50V, I <sub>D</sub> =20A,	-	62	-	nC	
Gate-Source Charge	Qgs		-	11	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	18	-		
Input Capacitance	Ciss	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V,	-	2658	-	pF	
Output Capacitance	Coss		-	381	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	24	-		
Gate resistance	Rg	f=1MHz	-	0.9	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =20A,	-	11	-		
Turn-On Rise Time	tr		-	16	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=10V, R_{G}=3\Omega$	-	52	-		
Turn-Off Fall Time	tf	(Note 2)	-	22	-		
Drain-Source Diode	•				•		
Diode Forward Current	Is	T 05°0	-	-	75	A	
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> =25°C	-	-	300		
Diode Forward Voltage	$V_{SD}$	Is=20A, V <sub>GS</sub> =0V	-	0.85	1.3	V	
Reverse Recovery Time	Trr	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	56	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	62	-	nC	

### NOTES:

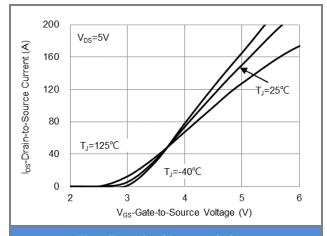
- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an  $R_{\theta JC}=1.8^{\circ}C/W$ .
- 4. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. E<sub>AS</sub> is calculated based on the condition of L=1mH, I<sub>AS</sub>=13A, V<sub>DD</sub>=30V, V<sub>GS</sub>=10V. 100% test at L=0.1mH, I<sub>AS</sub>=40A in production.
- 6. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**



**Fig.1 On-Region Characteristics** 



**Fig.2 Transfer Characteristics** 

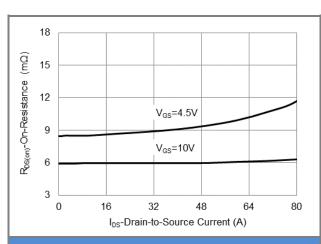


Fig.3 On-Resistance vs. Drain Current

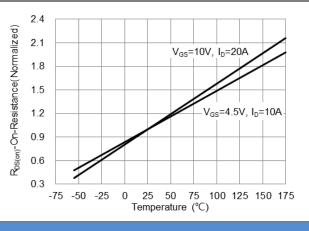
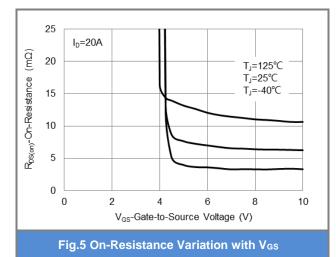


Fig.4 On-Resistance vs. Junction temperature



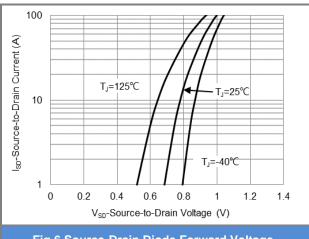


Fig.6 Source-Drain Diode Forward Voltage



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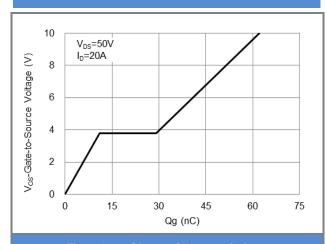


Fig.7 Gate-Charge Characteristics

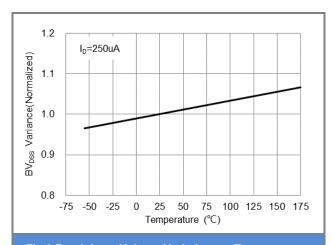


Fig.8 Breakdown Voltage Variation vs. Temperature

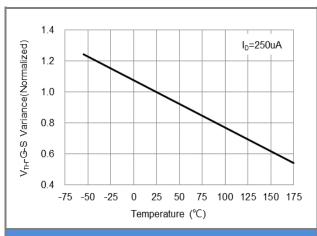


Fig.9 Threshold Voltage Variation with Temperature

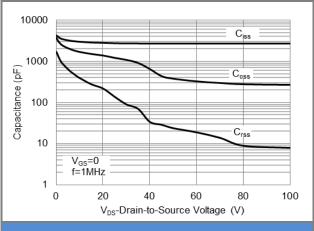
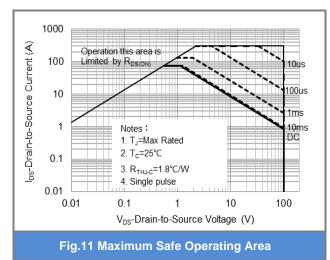
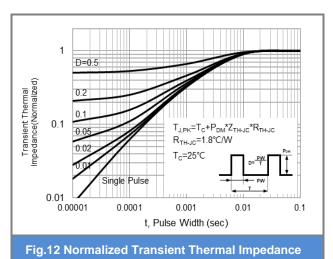


Fig.10 Capacitance vs. Drain-Source Voltage



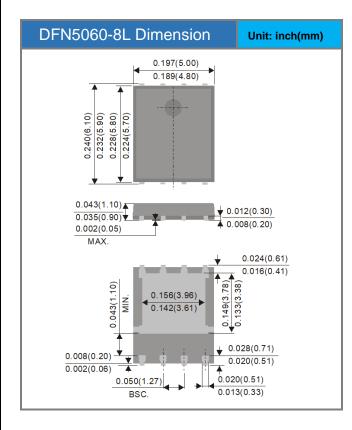


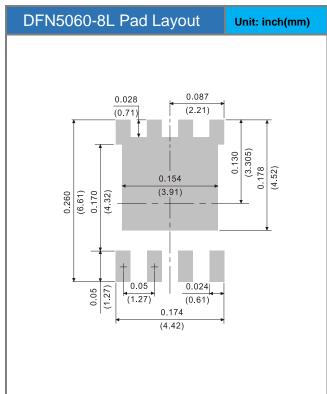


### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ5572A-AU	DFN5060-8L	3K pcs / 13" reel	Q5572A	

## **Packaging Information & Mounting Pad Layout**







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